

N-Channel Enhancement Mode MOSFET

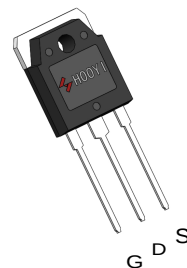
Features

- 100V/316A
 $R_{DS(ON)} = 2.1\text{ m}\Omega$ (typ.) @ $V_{GS} = 10\text{V}$
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Pin Description



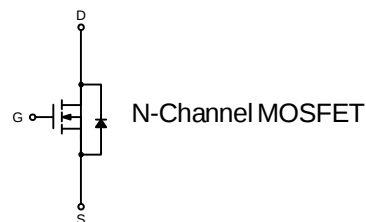
TO-247-3L



TO-3P-3L

Applications

- Power Management for Inverter Systems.



Ordering and Marking Information

 W HY5110 YYXXXJWW G	 A HY5110 YYXXXJWW G
	Package Code W : TO-247-3L A : TO-3P-3L Date Code YYXXX WW Assembly Material G : Lead Free Device

Note: HOOYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. HOOYI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. HOOYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HOOYI reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	316	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	T _C =25°C	1085**	A
I _D	Continuous Drain Current	T _C =25°C	316	A
		T _C =100°C	214	
P _D	Maximum Power Dissipation	T _C =25°C	500	W
		T _C =100°C	250	
R _{θJC}	Thermal Resistance-Junction to Case		0.3	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		40	
Avalanche Ratings				
E _{AS}	Avalanche Energy, Single Pulsed	L=0.5mH	2621***	mJ

Note : * Repetitive rating ; pulse width limited by junction temperature

** Drain current is limited by junction temperature

*** $V_D=80\text{V}$

Electrical Characteristics ($T_C = 25^{\circ}\text{C}$ Unless Otherwise Noted)

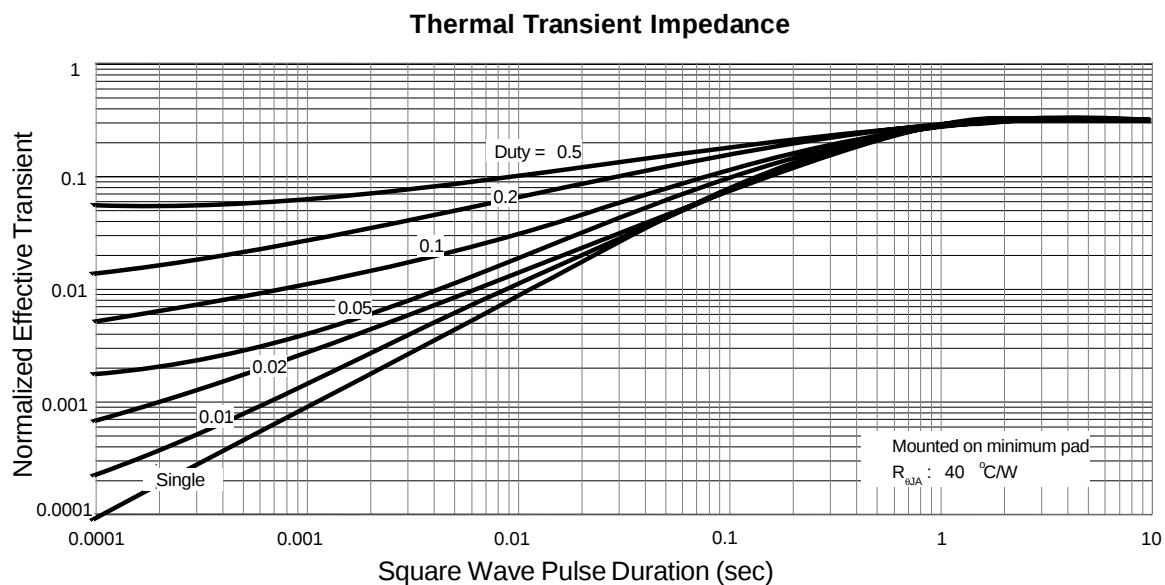
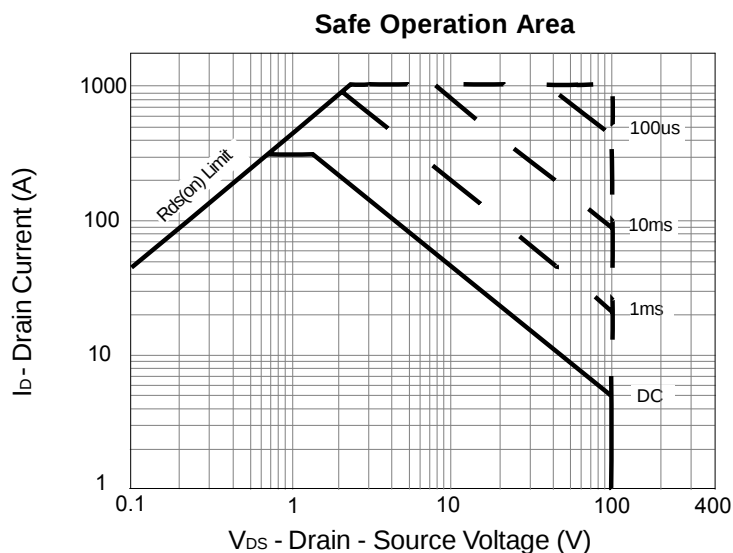
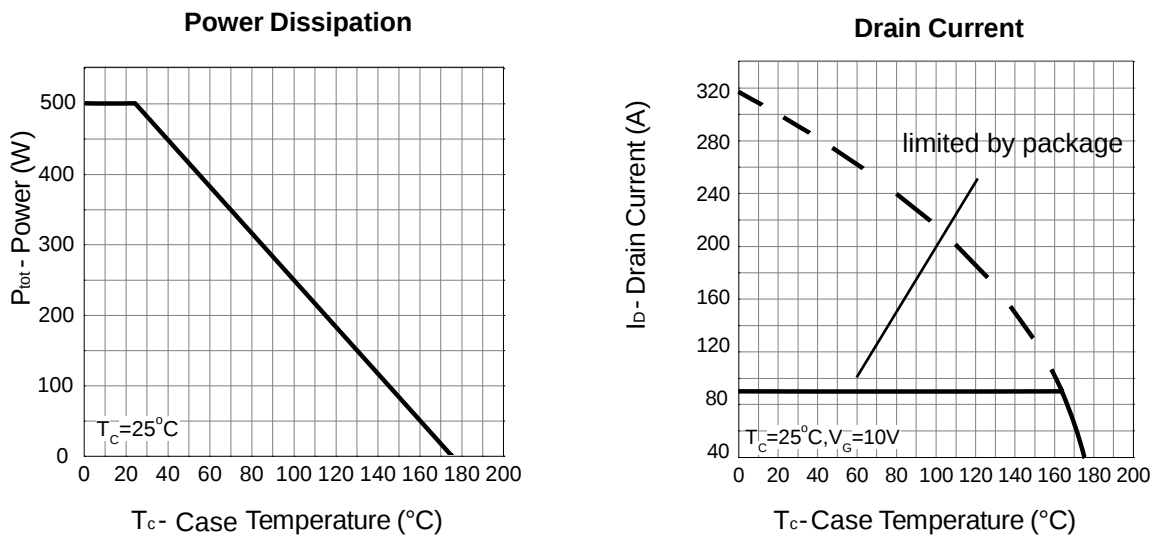
Symbol	Parameter	Test Conditions	HY5110			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	10	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =158A	-	2.1	2.5	mΩ
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =158 A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =158 A, dl _{SD} /dt=100A/μs	-	74	-	ns
Q _{rr}	Reverse Recovery Charge		-	138	-	nC

Electrical Characteristics (Cont.) ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY5110			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	0.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	16465	-	pF
C _{oss}	Output Capacitance		-	1558	-	
C _{rss}	Reverse Transfer Capacitance		-	850	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =50V, R _G =6 Ω, I _{DS} =158A, V _{GS} =10V,	-	58	-	ns
T _r	Turn-on Rise Time		-	49	-	
t _{d(OFF)}	Turn-off Delay Time		-	120	-	
T _f	Turn-off Fall Time		-	90	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =80V, V _{GS} =10V, I _{DS} =158A	-	356	-	nC
Q _{gs}	Gate-Source Charge		-	50	-	
Q _{gd}	Gate-Drain Charge		-	129	-	

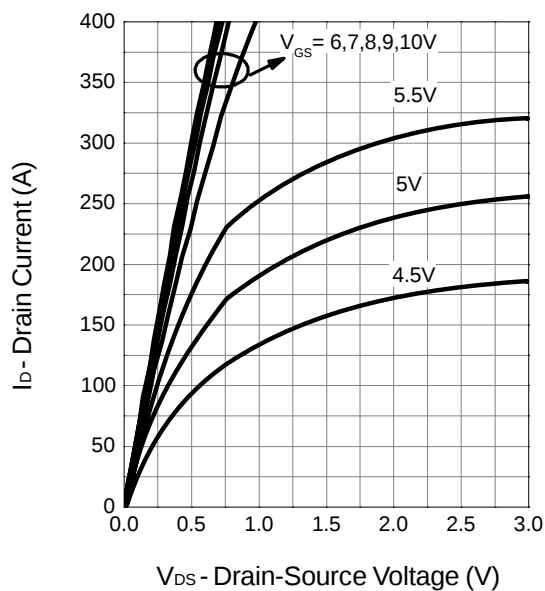
Note * : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Operating Characteristics

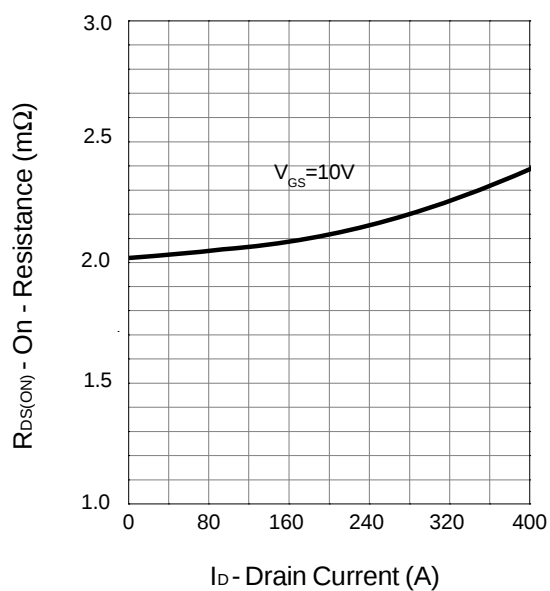


Typical Operating Characteristics (Cont.)

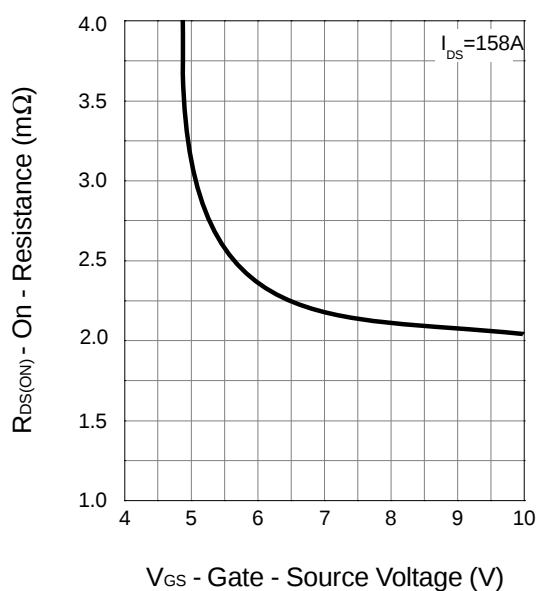
Output Characteristics



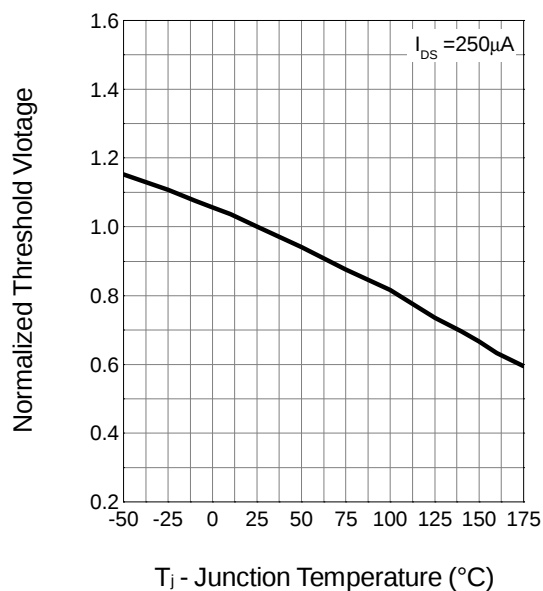
Drain-Source On Resistance



Drain-Source On Resistance

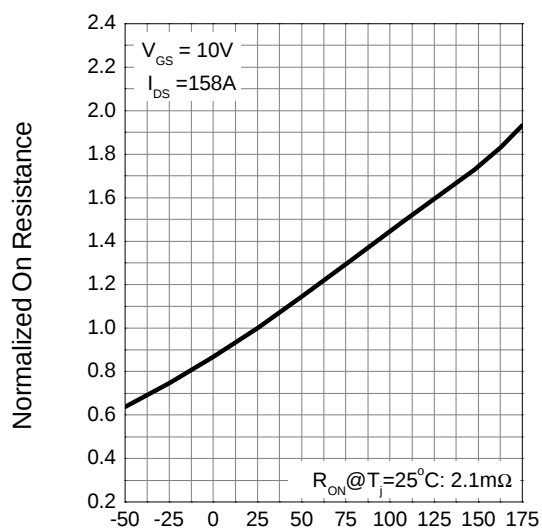


Gate Threshold Voltage



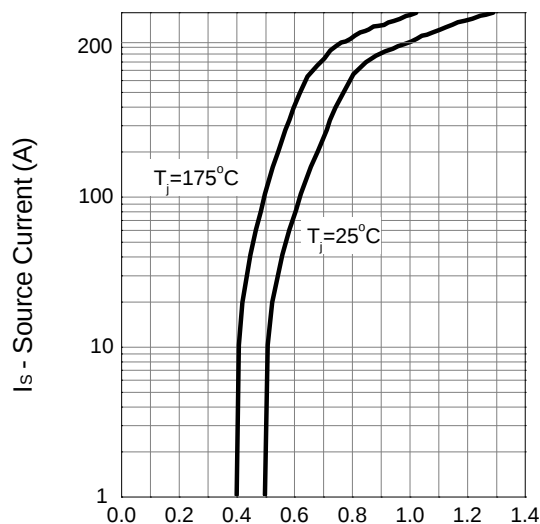
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance



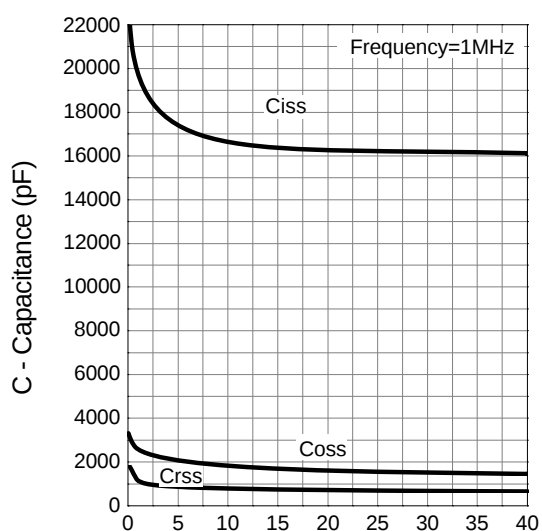
T_j - Junction Temperature ($^{\circ}\text{C}$)

Source-Drain Diode Forward



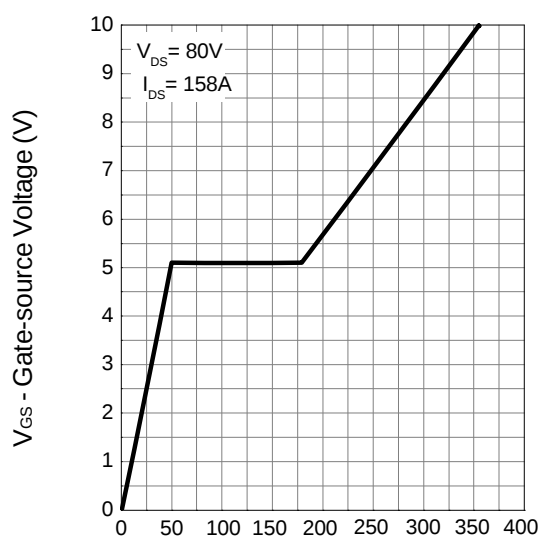
V_{SD} - Source-Drain Voltage (V)

Capacitance



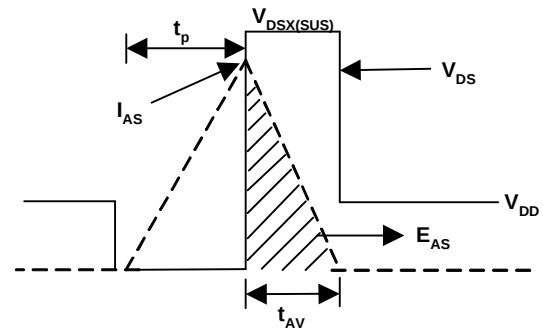
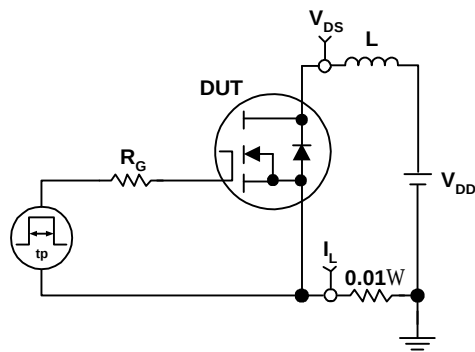
V_{DS} - Drain - Source Voltage (V)

Gate Charge

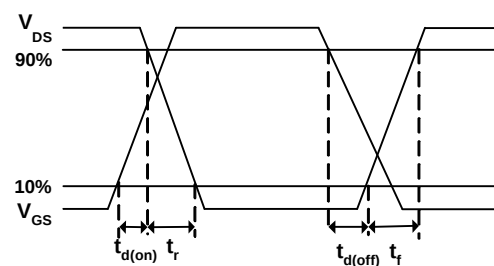
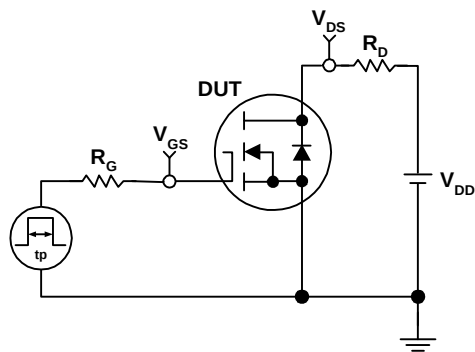


Q_G - Gate Charge (nC)

Avalanche Test Circuit and Waveforms

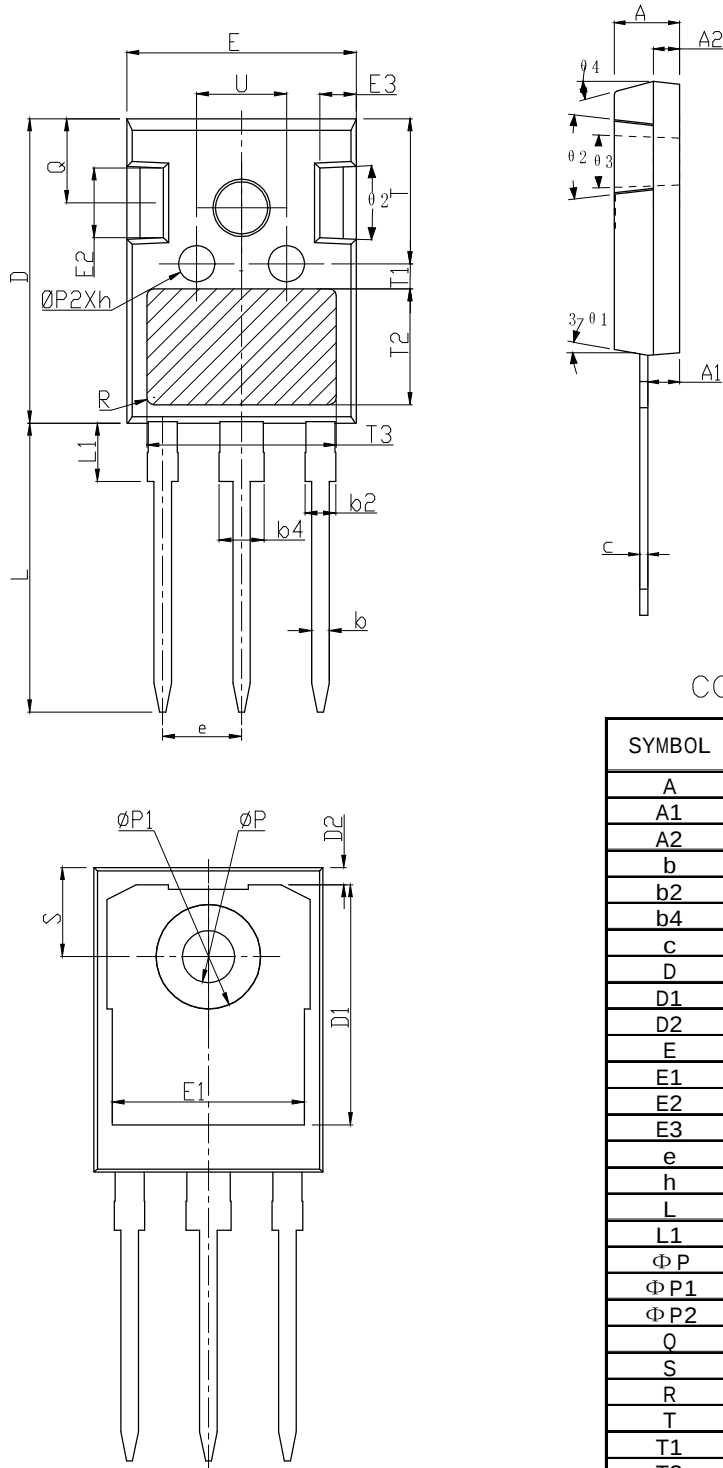


Avalanche Test Circuit and Waveforms



Package Information

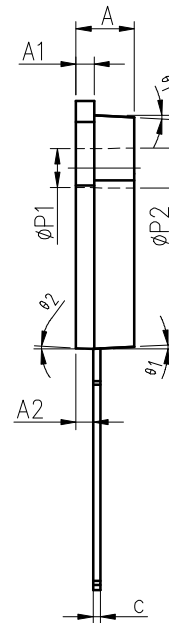
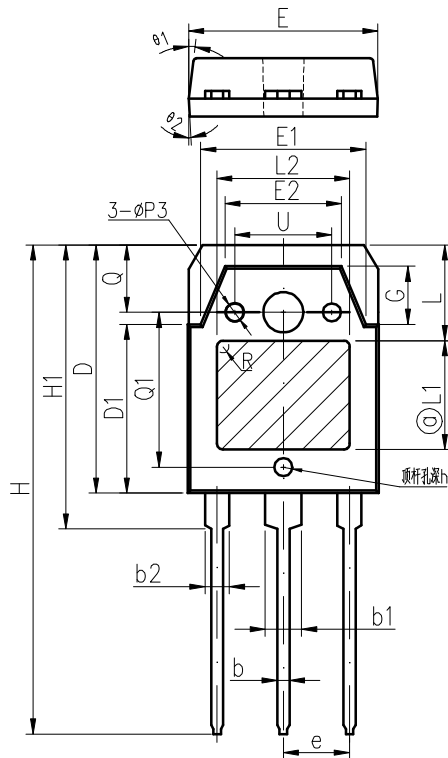
TO-247-3L



COMMON DIMENSIONS

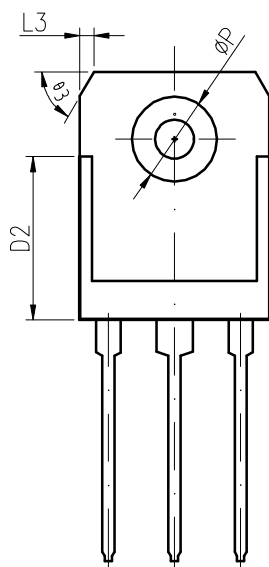
SYMBOL	mm		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16	1.21	1.26
b2	1.96	2.01	2.06
b4	2.96	3.01	3.06
c	0.59	0.61	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.44BSC		
h	0.05	0.10	0.15
L	19.80	19.92	20.10
L1	-	-	4.30
ΦP	3.50	3.60	3.70
ΦP1	-	-	7.30
ΦP2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S	6.15BSC		
R	0.50REF		
T	9.80	-	10.20
T1	1.65REF		
T2	8.00REF		
T3	12.80REF		
U	6.00	-	6.40
θ 1	6°	7°	8°
θ 2	4°	5°	6°
θ 3	1°	-	1.5°
θ 4	14°	15°	16°

TO-3P-3L



COMMON DIMENSIONS

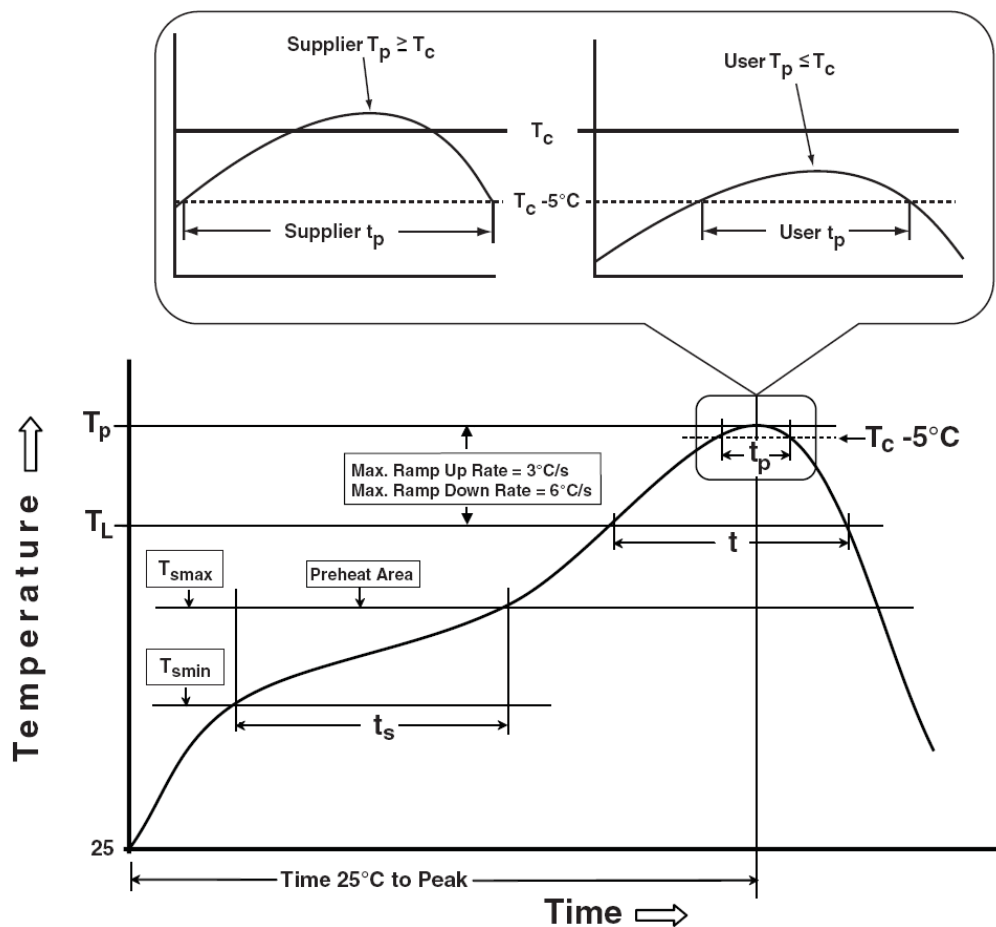
SYMBOL	mm		
	MIN	NOM	MAX
A	4.60	4.80	5.00
A1	1.40	1.50	1.60
A2	1.33	1.38	1.43
b	0.80	1.00	1.20
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
D	19.75	19.90	20.05
D1	13.70	13.90	14.10
D2	12.90 REF		
E	15.40	15.60	15.80
E1	13.40	13.60	13.80
E2	9.40	9.60	9.80
e	5.45 TYP		
G	4.60	4.80	5.00
H	40.30	40.50	40.70
H1	23.20	23.40	23.60
h	0.05	0.10	0.15
L	7.40 TYP		
L1	9.00 TYP		
L2	11.00 TYP		
L3	1.00 REF		
P	6.90	7.00	7.10
P1	3.20 REF		
P2	3.50 REF		
P3	1.40	1.50	1.60
R	0.50 REF		
Q	5.00 REF		
Q1	12.56	12.76	12.96
U	7.8	8	8.2
θ1	5°	7°	9°
θ2	1°	3°	5°
θ3	60° REF		



Devices Per Unit

Package Type	Unit	Quantity
TO-247-3L	Tube	30
TO-3P-3L	Tube	30

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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